

- Single Biasing Voltage (Self Biased)
- Frequency: 5 20GHz
- Small Signal Gain Typical : 25dB@6GHz 21dB@18GHz
- Gain Flatness: ±2.0dB Typical
- Noise Figure: 1.5dB Typical
- P1dB: 16dBm Typical
- Power Supply: +5V/80mA
- Input/Output: 50Ω
- Chip Size: 1.3 x 1.05 x 0.1mm

### **Typical Applications**

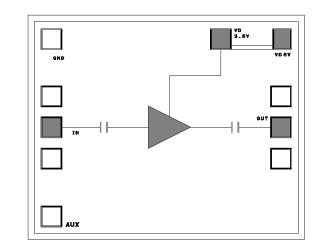
- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

## **Electrical Specifications**

#### TA = +25°C, VD = +5V, IDD = 80mA Typical

Parameters	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency	5-12		12-20			GHz	
Small Signal Gain	23	24		17	22		dB
Gain Flatness		±1.5			±1.7		dB
Noise Figure	1.4	1.5	2.5		1.5	2	dB
P1dB-Output 1dB Compression	14	16	18	12	17	18	dBm
Past - Saturated Output Power		19			19		dBm
OIP3- Output Third Order Intercept		30			30		dBm
Input Return Loss		8			8		dB
Output Return Loss		14			14		dB

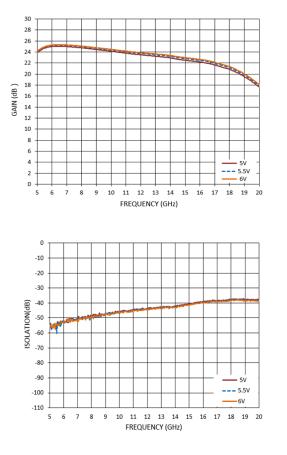
## **Functional Block Diagram**

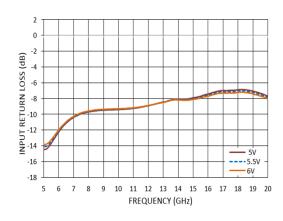


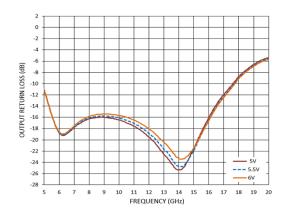
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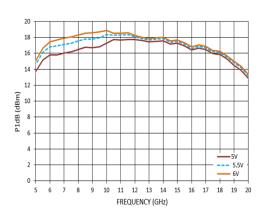
#### **Measurement Plots: S-parameters**



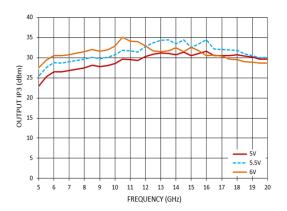




#### Measurement Plots: P1dB

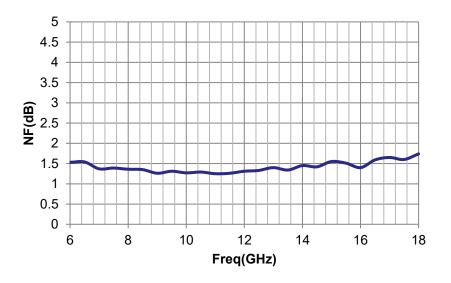


#### Measurement Plots: OIP3





#### Measurement Plots: Noise Figure



#### **Absolute Maximum Ratings**

Drain Bias Voltage (VD)	+7V
RF Input Power (RFIN)(VD=+5V)	+20dBm
Channel Temperature	150 °C
Continuous Pdiss (T = 85 °C)(derate 24 mW/°C above 85 °C)	25dBm
Thermal Resistance (channel to die bottom)	50°C/W
Operating Temperature	-55 to +85 °C
Storage Temperature	-65 to +150 °C

#### Typical Supply Current vs. Vdd

VD (V)	IDD (mA)
+5	80
+5.5	97
+6	120

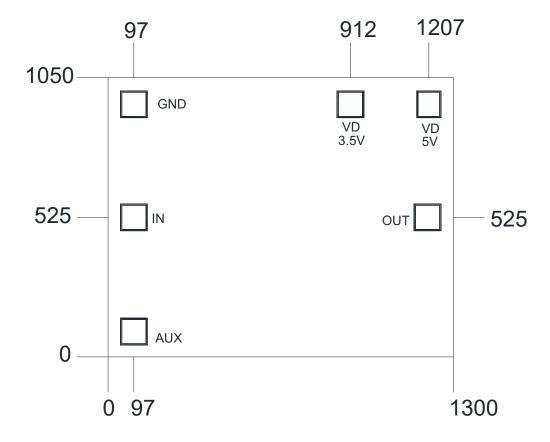


ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS



# **Outline Drawing:**

All Dimensions in  $\boldsymbol{\mu}\boldsymbol{m}$ 



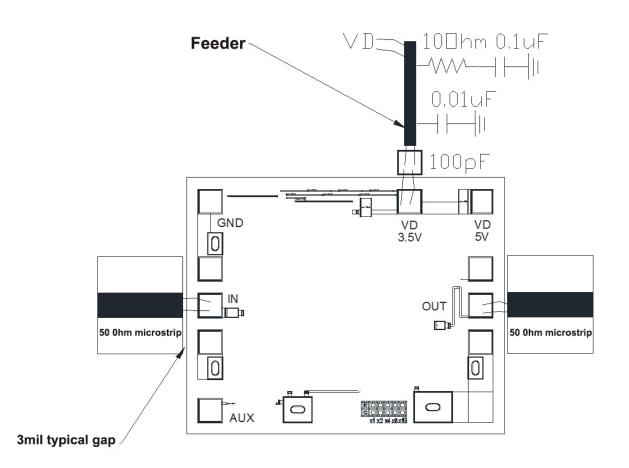
Notes:

- 1. Die thickness: 100um
- 2. DC bond pad is 100 x 100  $\mu m^2$
- 3. RF IN/OUT bond pad is 100 x 100  $\mu m^2$
- 4. DC bond pad is 100 x 100  $\mu m^2$
- 5. No DC Blocking Capacitor needed for RF input & RF output
- 6. Bond pad metalization: Gold
- 7. Backside metalization: Gold
- 8. Backside of the die (GND)

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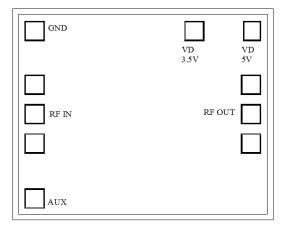


## **Assembly Drawing**



No	Function	Description
1	RF IN	Signal input terminal, connected to 50Ω circuit
2	RF OUT	Signal output terminal, connected to 50Ω circuit
3	VD	Connect to external 100pF and 0.01uF bypass capacitors.
9	GND1	Ground pad.





# **Biasing and Operation**

Performance is optimized when the drain voltage VD set to +5.0 V

#### **Turn ON procedure:**

- 1. Connect Input and Output with 50 Ohm source/load.
- 2. Apply positive drain voltage VD set to +5.0 V
- 3. Apply RF signal.

#### **Turn OFF procedure:**

- 1. Turn off RF signal
- 2. Turn off positive drain voltage VD

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